1. Record Nr. UNINA9910784415903321

Autore	Bulkowski Thomas N. <1957->
Titolo	Encyclopedia of chart patterns [[electronic resource] /] / Thomas N. Bulkowski
Pubbl/distr/stampa	Hoboken, NJ, : John Wiley, c2005
ISBN	1-118-04585-8 1-280-27588-X 9786610275885 0-471-72225-1
Edizione	[2nd ed.]
Descrizione fisica	1 online resource (xvii, 1012 pages : illustrations)
Collana	Wiley Trading
Disciplina	332.63/222
Soggetti	Stocks Commodity futures Investment analysis
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Includes index.
Nota di contenuto	Part One: Chart Patterns -- Part Two: Event Patterns -- Statistics Summary -- Glossary and Methodology.
Sommario/riassunto	In this revised and expanded second edition of the bestselling Encyclopedia of Chart Patterns, Thomas Bulkowski updates the classic with new performance statistics for both bull and bear markets and 23 new patterns, including a second section devoted to ten event patterns. Bulkowski tells you how to trade the significant events -- such as quarterly earnings announcements, retail sales, stock upgrades and downgrades -- that shape today's trading and uses statistics to back up his approach. This comprehensive new edition is a must-have reference if you're a technical investor or trader."--Provided by publisher.

2. Record Nr. UNINA9910785920503321

Titolo	CMOS nanoelectronics : innovative devices, architectures, and applications / / edited by Nadine Collaert
Pubbl/distr/stampa	Singapore : , : Pan Stanford Pub., , 2013
ISBN	0-429-11283-1 981-4364-03-7
Descrizione fisica	1 online resource (444 p.)
Altri autori (Persone)	CollaertNadine
Disciplina	621.3815
Soggetti	Molecular electronics Nanotechnology
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references.
Nota di contenuto	Front Cover; Contents; Preface; I. Integration of Multi-Gate Devices (FinFET); 1. Introduction to Multi-Gate Devices and Integration Challenges; 2. Dry Etching Patterning Requirements for Multi-Gate Devices; 3. High-k Dielectrics and Metal Gate Electrodes on SOI MuGFETs; 4. Doping, Contact and Strain Architectures for Highly Scaled FinFETs; II. Circuit-Related Aspects; 5. Variability and Its Implications for FinFET SRAM; 6. Specific Features of MuGFETs at High Temperatures over a Wide Frequency Range; 7. ESD Protection in FinFET Technology; III. Exploratory Devices and Characterization Tools 8. The Junctionless Nanowire Transistor9. The Variational Principle: A Valuable Ally Assisting the Self-Consistent Solution of Poisson's Equation and Semi-Classical Transport Equations; 10. New Tools for the Direct Characterisation of FinFETS; 11. Dopant Metrology in Advanced FinFETs
Sommario/riassunto	This book covers one of the most important device architectures that have been widely researched to extend the transistor scaling: FinFET. Starting with theory, the book discusses the advantages and the integration challenges of this device architecture. It addresses in detail the topics such as high-density fin patterning, gate stack design, and source/drain engineering, which have been considered challenges for the integration of FinFETs. The book also addresses circuit-related aspects, including the impact of variability on SRAM design, ESD

design, and high-T operation. It discusses a new d